

포항나노기술집적센터 장비이용수가표(2010.03)

(단위 : 원)

구분	관리번호	장비명(영문)	공정 Code	변경전(2009.10)			변경후(2010.03)				비고
				요금기준	USER 이용시	NCNT 엔지니어 서비스시	요금기준	기본가	USER 이용시	NCNT 엔지니어 서비스시	
Semiconductor (Photo)	SP01	E-Beam Lithography Sys - 1	SP01_01	60min	x	500,000	Hr	-	x	500,000	변경없음
	SP02	E-Beam Lithography Sys - 2	SP02_01	60min	x	450,000	Hr	-	x	450,000	변경없음
	SP03	Laser Lithography Sys	SP03_01	msak	x	400,000 (2um이상)/5inch	0매	-	x	300,000 (2um이상)/5inch	조정
	SP03	Laser Lithography Sys	SP03_02	msak	x	600,000 (2um이하)/5inch	0매	-	x	500,000 (2um이하)/5inch	조정
	SP03	Laser Lithography Sys	SP03_03	msak	x	800,000 (2um이상)/7inch	0매	-	x	500,000 (2um이상)/7inch	조정
	SP03	Laser Lithography Sys	SP03_04	msak	x	1,200,000 (2um이하)/7inch	0매	-	x	700,000 (2um이하)/7inch	조정
	SP03	Laser Lithography Sys	SP03_05	-	-	-	0매	-	x	400,000 (2um이상)/6inch	신규적용
	SP03	Laser Lithography Sys	SP03_06	-	-	-	0매	-	x	600,000 (2um이하)/6inch	신규적용
	SP03	Laser Lithography Sys	SP03_07	-	-	-	Hr	-	x	50,000 Mask Design 작업	신규적용
	SP04	I-Line Stepper	SP04_01	1 Hr	550,000	680,000	0매	100,000	x	40,000	조정
	SP05	PR Track	SP05_01	1Hr (재료 별도)	152,000	190,000	0매	100,000	x	40,000	조정
	SP05	PR Track	SP05_02	-	-	-	0매	100,000	x	40,000	신규적용
	SP06	EUV- IL Sys	-	-	-	-	-	-	-	-	미정
	SP07	EUV- IL PR Track	SP07_01	1Hr (재료 별도)	152,000	190,000	0매	100,000	x	40,000	조정
	SP07	EUV- IL PR Track	SP07_02	-	-	-	0매	100,000	x	40,000	신규적용
	SP08	Photo Base System	-	wafer	20,000	30,000	-	-	-	-	세분화
	SP08-1	PR Spin Coater	SP08-1_01	wafer	20,000	30,000	0매	-	30,000	40,000	조정
	SP08-1	PR Spin Coater	SP08-1_02	-	-	-	0매	-	25,000	30,000	신규적용
	SP08-2	Rinse & Dryer	SP08-2_01	wafer	30,000	50,000	0매	100,000	x	30,000	조정
	SP08-2	Rinse & Dryer	SP08-2_02	-	-	-	0매	100,000	x	30,000	신규적용
	SP08-3	Developer	SP08-3_01	wafer	50,000	70,000	0매	100,000	x	30,000	조정
	SP08-3	Developer	SP08-3_02	-	-	-	0매	100,000	x	30,000	신규적용
	SP08-4	Pt coater	SP08-4_01	회	x	50,000	0매	-	30,000	30,000	조정
	SP08-5	Wet Station_Organic	SP08-5_01	30min	20,000	30,000	0매	-	20,000	50,000	조정
	Semiconductor (Thin Film)	ST01	Atomic Layer Deposition	ST01_01	wafer	70,000	90,000	0매	-	170,000	200,000
ST02		UHV- CVD	ST02_01	wafer	x	100,000	0매	-	150,000	200,000	조정
ST03		Sputter - 1	ST03_01	wafer (재료 별도)	x	80,000	0매	-	x	70,000	조정
ST04		Sputter - 2	ST04_01	wafer (재료 별도)	64,000	80,000	0매	100,000	x	50,000	조정
ST04		Sputter - 2	ST04_02	-	-	-	0매	100,000	x	40,000	신규적용
ST04		Sputter - 2	ST04_03	-	-	-	0매	100,000	x	40,000	신규적용
ST05		AP- CVD	ST05_01	wafer	80,000	100,000	Lot	-	x	400,000	조정
ST06		LP- CVD System	-	wafer	x	80,000	-	-	-	-	세분화
ST06-1		LP- CVD	ST06-1_01	wafer	x	80,000	0매	100,000	x	70,000	조정
ST06-1		LP- CVD	ST06-1_02	-	-	-	0매	100,000	x	70,000	신규적용
ST06-1		LP- CVD	ST06-1_03	-	-	-	0매	100,000	x	70,000	신규적용
ST06-1		LP- CVD	ST06-1_04	-	-	-	0매	100,000	x	100,000	신규적용
ST06-2		Furnace	ST06-2_01	Lot	x	240,000	Lot	-	x	350,000	조정
ST07		PE- CVD- 1	ST07_01	wafer	x	100,000	0매	-	80,000	100,000	조정
ST07		PE- CVD- 1	ST07_02	-	-	-	0매	-	80,000	100,000	신규적용
ST08	Sputter- 3	ST08_01	wafer	40,000	50,000	0매	100,000	x	50,000	조정	
ST09	PE- CVD- 2	ST09_01	wafer	N/A	100,000	0매	100,000	x	50,000	조정	
ST09	PE- CVD- 2	ST09_02	-	-	-	0매	100,000	x	50,000	신규적용	
Semiconductor (Etch)	SE01	Dry Etcher_ICP	SE01_01	wafer	80,000	100,000	0매	-	80,000	100,000	변경없음
	SE01	Dry Etcher_ICP	SE01_02	-	-	-	0매	-	80,000	100,000	신규적용
	SE01	Dry Etcher_ICP	SE01_03	-	-	-	0매	-	80,000	100,000	신규적용
	SE02	Dry Etcher_20nm급	SE02_01	wafer	x	Aligner PR : 100000 E-Beam PR : 180000	0매	-	80,000	100,000	조정
	SE02	Dry Etcher_20nm급	SE02_02	-	-	-	0매	-	80,000	100,000	신규적용
	SE03	Dry Etcher_Oxide	SE03_01	wafer	80,000	100,000	0매	100,000	x	50,000	조정
	SE04	Dry Etcher_Poly Si	SE04_01	wafer	80,000	100,000	0매	100,000	x	50,000	조정
	SE05	PR Asher_BEOL	SE05_01	wafer	20,000	35,000	0매	100,000	x	50,000	조정
SE06	PR Asher_FEOL	SE06_01	wafer	28,000	35,000	0매	100,000	x	50,000	조정	
SE07	Dry Etcher_Metal	SE07_01	wafer	80,000	100,000	0매	100,000	x	50,000	조정	
Semiconductor (Wet)	SW01	Wet Station_Acid System	-	Lot (재료 별도)	30,000	40,000	-	-	-	-	세분화
	SW01-1	Wet Station_Acid	SW01-1_01	Lot (재료 별도)	30,000	40,000	Lot	-	80,000	100,000	조정
	SW01-1	Wet Station_Acid	SW01-1_02	-	-	-	Lot	-	80,000	100,000	신규적용
	SW01-1	Wet Station_Acid	SW01-1_03	-	-	-	Lot	-	120,000	150,000	신규적용
	SW01-2	Spin Dryer	SW01-2_01	회	무료	무료	Lot	-	10,000	10,000	조정
	SW02	Wet Station_Pre Clean- 1	SW02_01	Lot (재료 별도)	40,000	50,000	Lot	-	x	250,000	조정
	SW03	Wet Station_SPM	SW03_01	Lot (재료 별도)	40,000	50,000	Lot	-	x	250,000	조정
SW04	Wet Station_전처리- 2	SW04_01	Lot (재료 별도)	40,000	50,000	Lot	-	x	250,000	조정	
Semiconductor (Diffusion)	SD01	Furnace_Low T Ann.	SD01_01	Lot (4.5H기준)	360,000	400,000	Lot	-	x	200,000	조정
	SD02	Furnace_+ Dopant Ann.	SD02_01	Lot (4.5H기준)	360,000	400,000	Lot	-	x	400,000	조정
	SD03	Furnace_Poly Si	SD03_01	Lot	390,000	410,000	Lot	-	x	450,000	조정
	SD04	Furnace_High T Anneal	SD04_01	Lot (4.5H기준)	320,000	400,000	Lot	-	x	480,000	조정
	SD05	Furnace_Dry Oxidation	SD05_01	Lot (4.5H기준)	320,000	400,000	Lot	-	x	400,000	조정
	SD06	Furnace_Pyro Oxidation System	-	Lot (4.5H기준)	320,000	400,000	-	-	-	-	세분화
	SD06-1	Furnace_Pyro Oxidation	SD06-1_01	Lot (4.5H기준)	320,000	400,000	Lot	-	x	400,000	조정
	SD07	RTP for RTO	SD07_01	Wafer	40,000	50,000	0매	100,000	40,000	50,000	조정
	SD08	RTP for Silicide	SD08_01	Wafer	40,000	50,000	0매	100,000	40,000	50,000	조정
	SD09	High Current Implanter	SD09_01	wafer	48,000	60,000	Lot	-	x	300,000	조정
SD10	Medium Current Implanter	SD10_01	wafer	48,000	60,000	0매	100,000	x	50,000	조정	
Semiconductor (Measurement)	SM01	CD- SEM	SM01_01	1 Hour	192,000	240,000	0매	-	x	50,000	조정
	SM01	CD- SEM	SM01_02	-	-	-	0매	-	x	50,000	신규적용
	SM02	Process Monitoring System	-	30min	30,000	40,000	-	-	-	-	세분화
	SM02-1	Spectroscopic Ellipsometer	SM02-1_01	30min	30,000	40,000	0매	-	30,000	30,000	조정
SM02-2	4 Point Probe- 1	SM02-2_01	30min	20,000	30,000	0매	-	20,000	20,000	조정	

구분	관리번호	장비명(영문)	공정 Code	변경전(2009.10)			변경후(2010.03)				비고
				요율기준	USER 이용시	NCNT 엔지니어 서비스시	요율기준	기본가	USER 이용시	NCNT 엔지니어 서비스시	
Semiconductor (Measurement)	SM02-3	3D Profiler	SM02-3_01	30min	20,000	30,000	매	-	20,000	30,000	조정
	SM02-4	Stress Measurement System	SM02-4_01	30min	10,000	20,000	매	-	20,000	30,000	조정
	SM02-10	4 Point Probe- 2	SM02-10_01	-	-	-	매	-	10,000	20,000	신규적용
	SM03	Thickness Measurement	SM03_01	30min	24,000	30,000	매	-	x	10,000	조정
	SM04	EUV Aerial Image Microscope(AIMS)	SM04_01	Hr	x	300,000	Hr	-	x	300,000	변경없음
	SM05	EUV Reflectometry	SM05_01	Hr	x	200,000	Hr	-	x	200,000	변경없음
	SM06	Cryogenic RF Measurement System	SM06_01	Hr	108,000	121,000	Hr	-	100,000	120,000	조정
	SM07	Flicker Noise Measurement System	SM07_01	Hr	89,000	102,000	Hr	-	100,000	120,000	조정
	SM08	FT- IR	SM08_01	30min	24,000	30,000	매	-	20,000	30,000	조정
Semiconductor (Nanomaterial)	SN01	CNT Synthesis System	-	-	-	-	-	-	-	-	세분화
	SN01-1	CNT Synthesis CVD	SN01-1_01	CVD, hr	50,000	70,000	CVD, hr	-	50,000	70,000	변경없음
	SN01-1	CNT Synthesis CVD	SN01-1_02	Furnace, hr	16,000	20,000	Furnace, hr	-	16,000	20,000	변경없음
	SN01-1	CNT Synthesis CVD	SN01-1_03	UV- Nir, 시료	12,000	16,000	UV- Nir, 시료	-	12,000	16,000	변경없음
	SN01-1	CNT Synthesis CVD	SN01-1_04	Centrifuge, 배치당	12,000	16,000	Centrifuge, 배치당	-	12,000	16,000	변경없음
	SN02	Nanocrystal- Synthesis System	SN02_01	wafer	60,000	80,000	매	-	60,000	80,000	변경없음
NEMS	NP01	Mask Aligner for NEMS	NP01_01	wafer	60,000	80,000	매	-	50,000	60,000	조정
	NP01	Mask Aligner for NEMS	NP01_02	-	-	-	매	-	50,000	60,000	신규적용
	NP02	NEMS Base System	-	30min	30,000	40,000	-	-	-	-	세분화
	NP02-1	Spin Coater 1	NP02-1_01	-	-	-	매	-	20,000	30,000	신규적용
	NP02-2	Spin Coater 2	NP02-2_01	-	-	-	매	-	30,000	40,000	신규적용
	NP02-2	Spin Coater 2	NP02-2_02	-	-	-	매	-	20,000	30,000	신규적용
	NP02-3	Wet station 1	NP02-3_01	-	-	-	매	-	20,000	30,000	신규적용
	NP02-3	Wet station 1	NP02-3_02	-	-	-	매	-	20,000	30,000	신규적용
	NP02-15	PR Asher for NEMS	NP02-15_01	wafer	20,000	35,000	매	-	30,000	50,000	조정
	NT01	E- Beam Evaporator	NT01_01	회 (재료별도)	50,000	60,000	Lot	-	x	250,000	조정
	NT01	E- Beam Evaporator	NT01_02	-	-	-	Lot	-	x	150,000	신규적용
	NT02	PZT Coater	NT02_01	wafer(재료별도)	40,000	50,000	매	100,000	x	40,000	조정
	NE01	Deep Reactive Ion Etcher	NE01_01	50um (10um추가시)	100,000 10,000	150,000 20,000	매	-	120,000	150,000	조정
	NE02	PZT Etcher	NE02_01	wafer	60,000	80,000	매	-	80,000	100,000	조정
	Display	DP01	Spin Coater with Glove Box	DP01_01	Hr	15,000	20,000	매	-	30,000	40,000
DP02		Mask Aligner	DP02_01	wafer	70,000	90,000	매	-	60,000	70,000	조정
DP03		Display Photo Base System	-	-	-	-	-	-	-	-	세분화
DP03-1		Glass Cleaner System	DP03-1_01	회	30,000	40,000	매	-	20,000	30,000	조정
DP03-1		Glass Cleaner System	DP03-1_02	-	-	-	매	-	20,000	30,000	신규적용
DP03-2		Spin Developer	DP03-2_01	회	30,000	40,000	매	-	20,000	30,000	조정
DT01		Ink Jet Printing System	DT01_01	Hr (재료별도)	22,000	35,000	매	-	30,000	40,000	조정
DT02		OMBD & Metal Evaporation System	-	-	-	-	-	-	-	-	세분화
DT02-1		OMBD & Thermal Evaporator	DT02-1_01	Hr (재료별도)	100,000	130,000	매	-	100,000	150,000	조정
DT02-2		Metal Evaporator	DT02-2_01	Hr (재료별도)	100,000	130,000	매	-	100,000	150,000	조정
DT03		OLED Evaporation System	-	-	-	-	-	-	-	-	세분화
DT03-1		OLED Evaporator- 1	DT03-1_01	Hr (재료별도)	160,000	190,000	매	-	160,000	190,000	조정
DT04		PECVD System	DT04_01	wafer	80,000	110,000	매	-	120,000	150,000	조정
DT04		PECVD System	DT04_02	-	-	-	매	-	120,000	150,000	신규적용
DM01		OLED Probe Station with Glove Box	DM01_01	Hr	35,000	50,000	매	-	70,000	100,000	조정
DM01-1		OLED Probe Station	DM01-1_01	Hr	35,000	50,000	매	-	70,000	100,000	조정
DM01-2		Glove Box	DM01-2_01	-	-	-	매	-	70,000	100,000	신규적용
DM01-3		I- V Meter	DM01-3_01	-	-	-	매	-	70,000	100,000	신규적용
DM01-4		Low Temp. Probstation Sys	DM01-4_01	Hr	35,000	50,000	매	-	70,000	100,000	조정
DM02		Surface Potential Measurement Sys	DM02_01	Hr	70,000	100,000	매	-	100,000	140,000	조정
Measurement & Analysis	MM01	HR FE- SEM	MM01_01	Hr	50,000	70,000	Hr	-	50,000	70,000	변경없음
	MM02	Focused Ion Beam System	MM02_01	Hr SEM만 이용시	200,000 50,000	200,000 50,000	Hr SEM만 이용시	-	200,000 50,000	200,000 50,000	변경없음
	MM02-1	Focused Ion Beam System - 1	MM02-1_01	Hr SEM만 이용시	200,000 50,000	200,000 50,000	Hr SEM만 이용시	-	200,000 50,000	200,000 50,000	변경없음
	MM03	3D Total Analysis System	MM03_01	Hr	x	200,000	Hr	-	x	200,000	변경없음
	MM04	Cs Corrected HR STEM 1	MM04_01	Hr	x	250,000	Hr	-	x	250,000	변경없음
	MM05	Cs Corrected HR STEM 2	MM05_01	Hr	x	250,000	Hr	-	x	250,000	변경없음
	MM06	3 Dimensional Atom Probe	MM06_01	시료당 (5시간 기본) 시료당(<0.3 M ions)	x	200,000	시료당 (5시간 기본) 시료당(<0.3 M ions)	-	x	200,000	변경없음
	MM06	3 Dimensional Atom Probe	MM06_02	시료당 (5시간 기본) 시료당(>0.3 M ions)	x	1,000,000	시료당 (5시간 기본) 시료당(>0.3 M ions)	-	x	1,000,000	변경없음
	MM07	SPM System	MM07_01	Hr (재료별도)	x	50,000	Hr (재료별도)	-	x	50,000	변경없음
	MM07-1	AFM	MM07-1_01	Hr (재료별도)	x	50,000	Hr (재료별도)	-	x	50,000	변경없음
	MM08	Multi- mode STM & AFM	MM08_01	Hr (재료별도)	x	50,000	Hr (재료별도)	-	x	50,000	변경없음
	MM08-1	UHV- LT STM	MM08-1_01	Hr (재료별도)	x	50,000	Hr (재료별도)	-	x	50,000	변경없음
	MM09	Secondary Ion Mass Spectrometry	MM09_01	시료당(1시간 기 본) Mass Spectrum Depth	x	100,000	시료당(1시간 기 본) Mass Spectrum Depth	-	x	100,000	변경없음
	MM09	Secondary Ion Mass Spectrometry	MM09_02	시료당(1시간 기 본) PI/Imaging	x	120,000	시료당(1시간 기 본) PI/Imaging	-	x	120,000	변경없음
	MC01	Magnetic Property Measurement Sys.	MC01_01	Hr	15,000	20,000	Hr	-	15,000	20,000	변경없음
	MC02	Low Temp Probe Station	MC02_01	Hr (재료별도)	15,000	20,000	Hr (재료별도)	-	15,000	20,000	변경없음
	MC03	Variable Temperature Insert	MC03_01	Hr (재료별도)	15,000	20,000	Hr (재료별도)	-	15,000	20,000	변경없음
	MS01	Sample Preparation System	-	-	-	-	-	-	-	-	세분화
	MS01	Sample Preparation System (Si-TEM)	MS01_01	-	-	-	시료당 (4시간)	-	x	100,000	신규적용
	MS01	Sample Preparation System (Steel-TEM)	MS01_02	-	-	-	시료당 (3시간)	-	x	60,000	신규적용
	MS01	Sample Preparation System (EBSD)	MS01_03	-	-	-	시료당 (4시간)	-	x	80,000	신규적용
	MS01-1	Cutting/Grinding/Polishing System	MS01-1_01	시료당 30min	x	60,000 10,000	시료당 30min	-	x	60,000 10,000	변경없음
	MS01-2	Gentle Mill	MS01-2_01	15min	20,000	20,000	15min	-	20,000	20,000	변경없음
MS01-3	Ion Beam Thinner	MS01-3_01	15min	10,000	10,000	15min	-	10,000	10,000	변경없음	